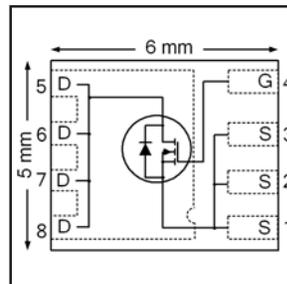


HEXFET® Power MOSFET

| | | |
|---|-------------|-----------|
| V_{DS} | 100 | V |
| R_{DS(on) max} (@V _{GS} = 10V) | 14.9 | mΩ |
| Q_g (typical) | 40 | nC |
| R_G (typical) | 1.7 | Ω |
| I_D (@T _{c(Bottom)} = 25°C) | 55 | A |



Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

Features and Benefits

Features

| |
|--|
| Low R _{DSon} (≤ 14.9mΩ at V _{gs} = 10V) |
| Low Thermal Resistance to PCB (≤ 1.2°C/W) |
| 100% R _g tested |
| Low Profile (≤ 0.9 mm) |
| Industry-Standard Pinout |
| Compatible with Existing Surface Mount Techniques |
| RoHS Compliant Containing no Lead, no Bromide and no Halogen |
| MSL1, Industrial Qualification |

results in

⇒

Benefits

| |
|------------------------------------|
| Lower Conduction Losses |
| Enables better thermal dissipation |
| Increased Reliability |
| Increased Power Density |
| Multi-Vendor Compatibility |
| Easier Manufacturing |
| Environmentally Friendlier |
| Increased Reliability |

| Orderable part number | Package Type | Standard Pack | | Note |
|-----------------------|----------------|---------------|----------|-----------------|
| | | Form | Quantity | |
| IRFH5210TRPBF | PQFN 5mm x 6mm | Tape and Reel | 4000 | |
| IRFH5210TR2PBF | PQFN 5mm x 6mm | Tape and Reel | 400 | EOL notice #259 |

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---|--|--------------|-------|
| V _{DS} | Drain-to-Source Voltage | 100 | V |
| V _{GS} | Gate-to-Source Voltage | ±20 | |
| I _D @ T _A = 25°C | Continuous Drain Current, V _{GS} @ 10V | 10 | A |
| I _D @ T _A = 70°C | Continuous Drain Current, V _{GS} @ 10V | 8.1 | |
| I _D @ T _{c(Bottom)} = 25°C | Continuous Drain Current, V _{GS} @ 10V | 55 | |
| I _D @ T _{c(Bottom)} = 100°C | Continuous Drain Current, V _{GS} @ 10V | 35 | |
| I _{DM} | Pulsed Drain Current ① | 220 | |
| P _D @ T _A = 25°C | Power Dissipation ⑤ | 3.6 | W |
| P _D @ T _{c(Bottom)} = 25°C | Power Dissipation ⑤ | 104 | |
| | Linear Derating Factor ⑤ | 0.029 | W/°C |
| T _J | Operating Junction and Storage Temperature Range | -55 to + 150 | °C |
| T _{STG} | | | |

Notes ① through ⑤ are on page 9

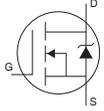
Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-------------------------------------|---|------|------|------|-------|--|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | 100 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.10 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 12.6 | 14.9 | mΩ | V _{GS} = 10V, I _D = 33A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | — | 4.0 | V | V _{DS} = V _{GS} , I _D = 100μA |
| ΔV _{GS(th)} | Gate Threshold Voltage Coefficient | — | -9.3 | — | mV/°C | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 100V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 100V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |
| g _{fs} | Forward Transconductance | 66 | — | — | S | V _{DS} = 50V, I _D = 33A |
| Q _g | Total Gate Charge | — | 40 | 60 | nC | V _{DS} = 50V V _{GS} = 10V I _D = 33A See Fig.17 & 18 |
| Q _{gs1} | Pre-V _{th} Gate-to-Source Charge | — | 7.4 | — | | |
| Q _{gs2} | Post-V _{th} Gate-to-Source Charge | — | 3.2 | — | | |
| Q _{gd} | Gate-to-Drain Charge | — | 11 | — | | |
| Q _{godr} | Gate Charge Overdrive | — | 18.4 | — | | |
| Q _{sw} | Switch Charge (Q _{gs2} + Q _{gd}) | — | 14.2 | — | | |
| Q _{oss} | Output Charge | — | 11 | — | nC | V _{DS} = 16V, V _{GS} = 0V |
| R _G | Gate Resistance | — | 1.7 | — | Ω | |
| t _{d(on)} | Turn-On Delay Time | — | 7.2 | — | ns | V _{DD} = 50V, V _{GS} = 10V I _D = 33A R _G = 1.65Ω See Fig.15 |
| t _r | Rise Time | — | 9.7 | — | | |
| t _{d(off)} | Turn-Off Delay Time | — | 21 | — | | |
| t _f | Fall Time | — | 6.5 | — | | |
| C _{iss} | Input Capacitance | — | 2570 | — | pF | V _{GS} = 0V V _{DS} = 25V f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 260 | — | | |
| C _{rss} | Reverse Transfer Capacitance | — | 100 | — | | |

Avalanche Characteristics

| | Parameter | Typ. | Max. | Units |
|-----------------|---------------------------------|------|------|-------|
| E _{AS} | Single Pulse Avalanche Energy ② | — | 86 | mJ |
| I _{AR} | Avalanche Current ① | — | 33 | A |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|--|---|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) ⑥ | — | — | 55 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 220 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 33A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 29 | 44 | ns | T _J = 25°C, I _F = 33A, V _{DD} = 50V |
| Q _{rr} | Reverse Recovery Charge | — | 165 | 250 | nC | di/dt = 500A/μs ③ |
| t _{on} | Forward Turn-On Time | Time is dominated by parasitic Inductance | | | | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|---------------------------|-----------------------|------|------|-------|
| R _{θJC} (Bottom) | Junction-to-Case ④ | — | 1.2 | °C/W |
| R _{θJC} (Top) | Junction-to-Case ④ | — | 15 | |
| R _{θJA} | Junction-to-Ambient ⑤ | — | 35 | |
| R _{θJA} (<10s) | Junction-to-Ambient ⑤ | — | 22 | |

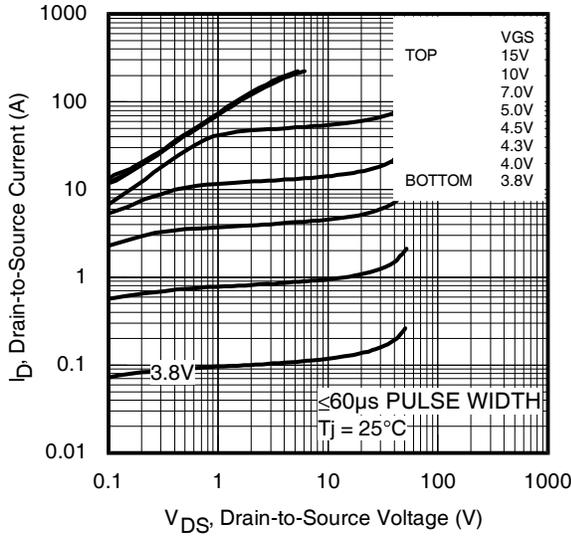


Fig 1. Typical Output Characteristics

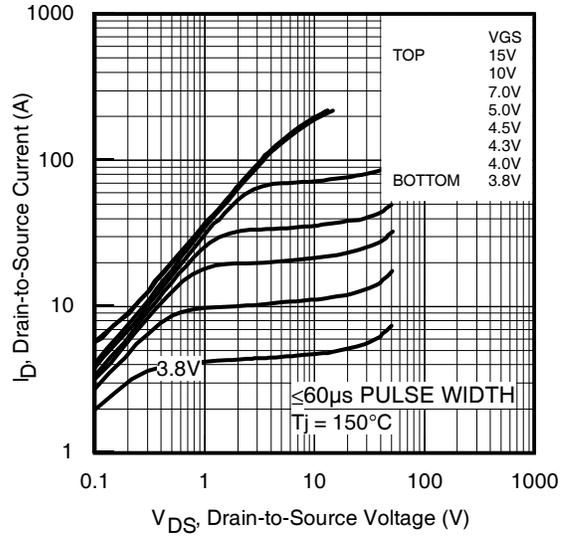


Fig 2. Typical Output Characteristics

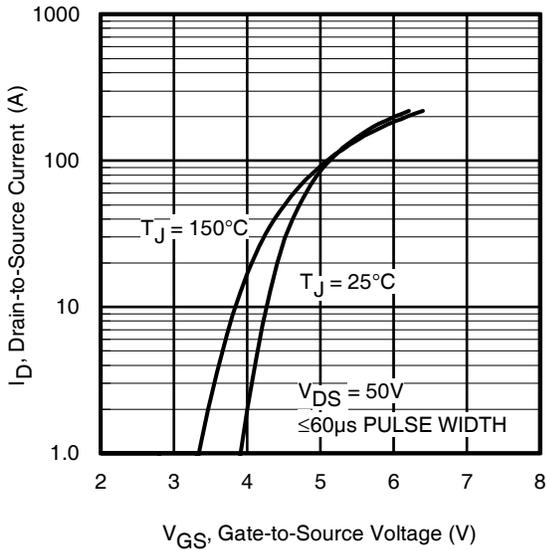


Fig 3. Typical Transfer Characteristics

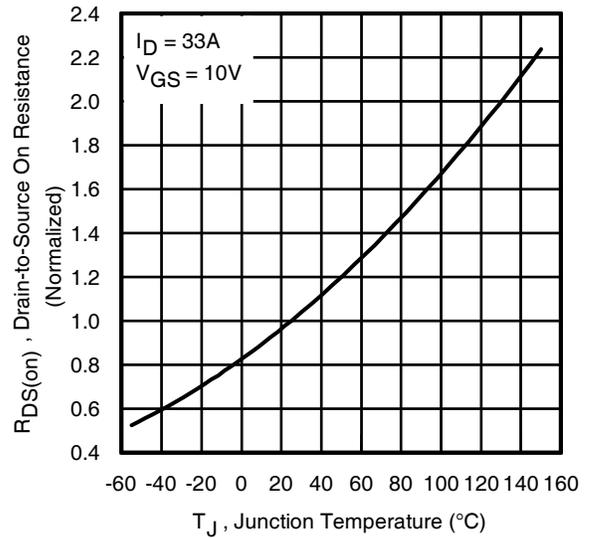


Fig 4. Normalized On-Resistance vs. Temperature

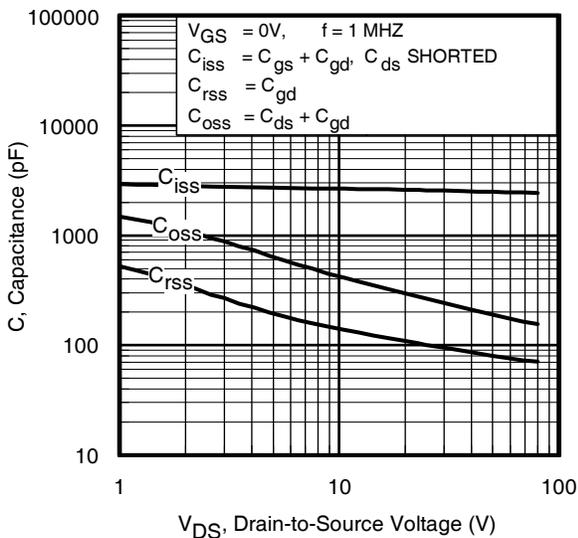


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

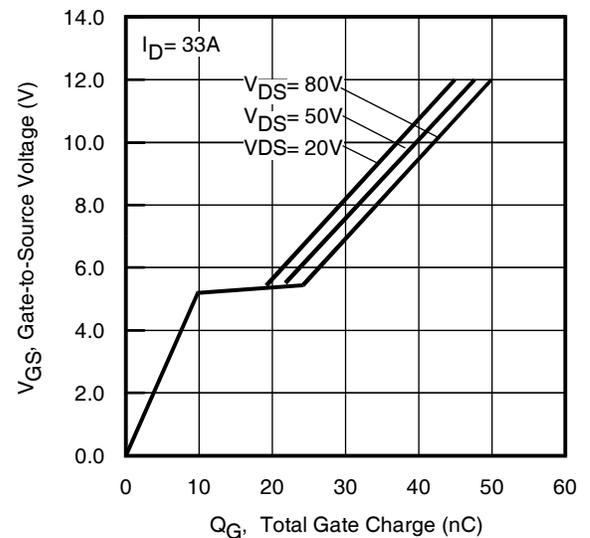


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

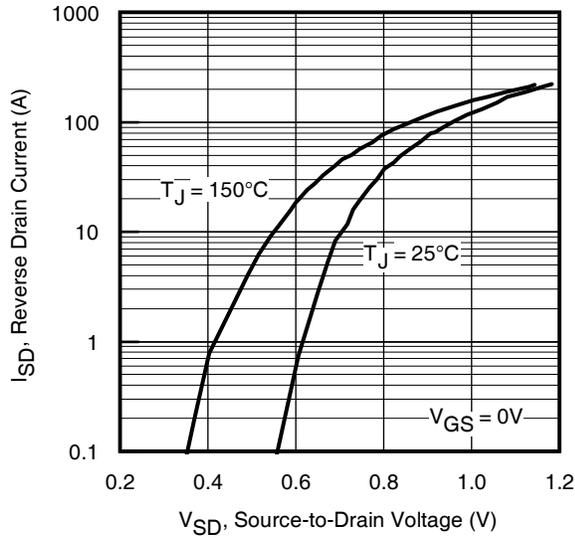


Fig 7. Typical Source-Drain Diode Forward Voltage

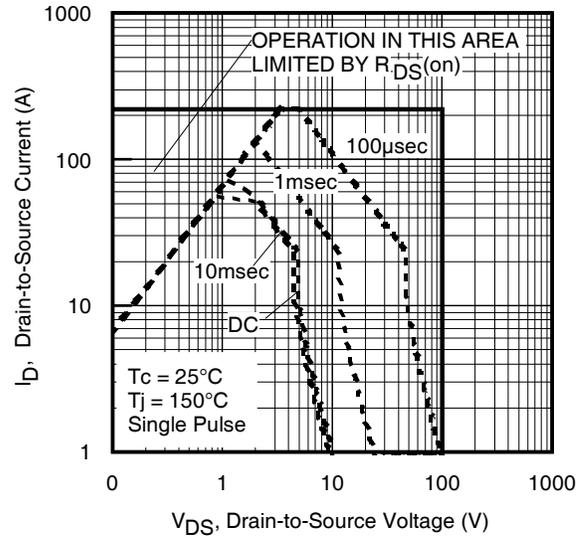


Fig 8. Maximum Safe Operating Area

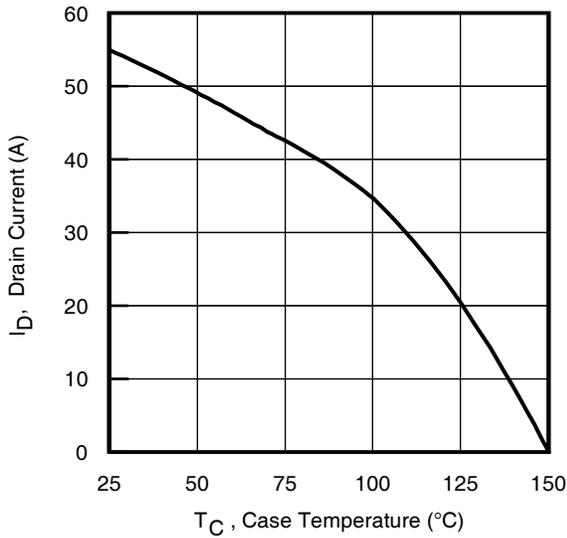


Fig 9. Maximum Drain Current vs. Case (Bottom) Temperature

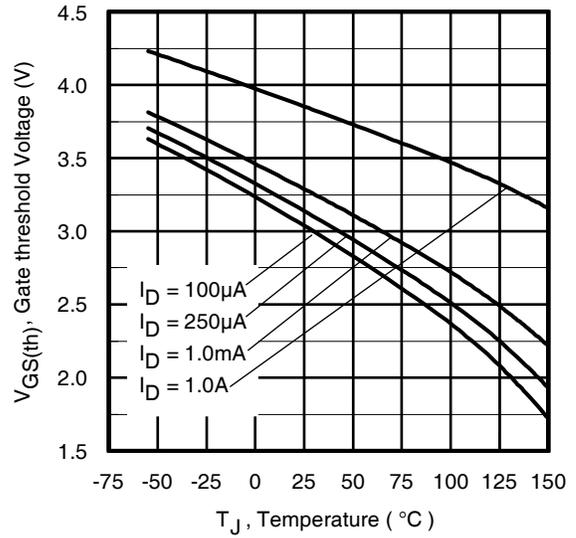


Fig 10. Threshold Voltage vs. Temperature

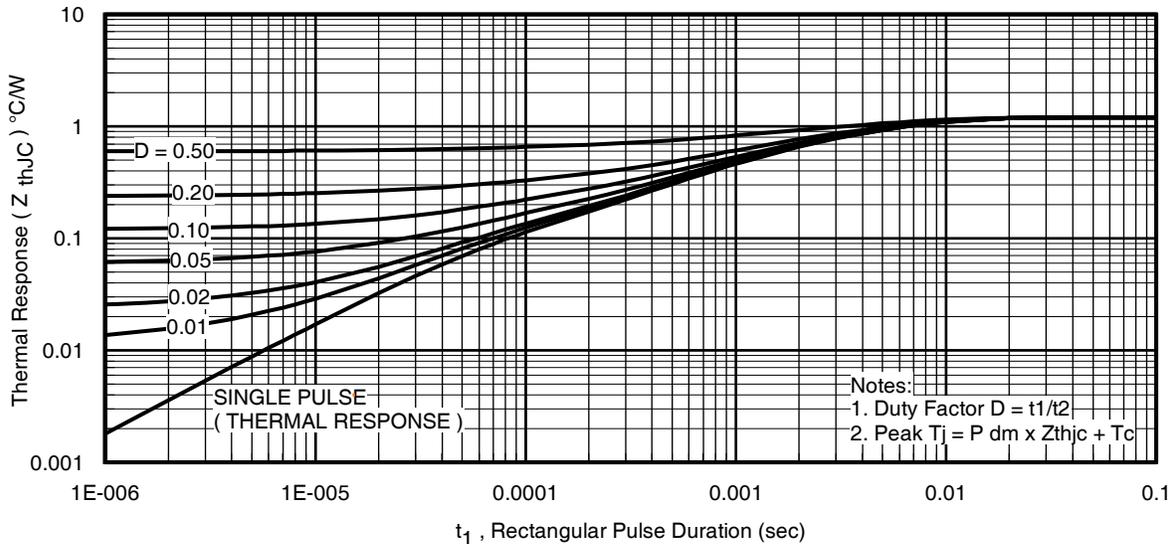


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)

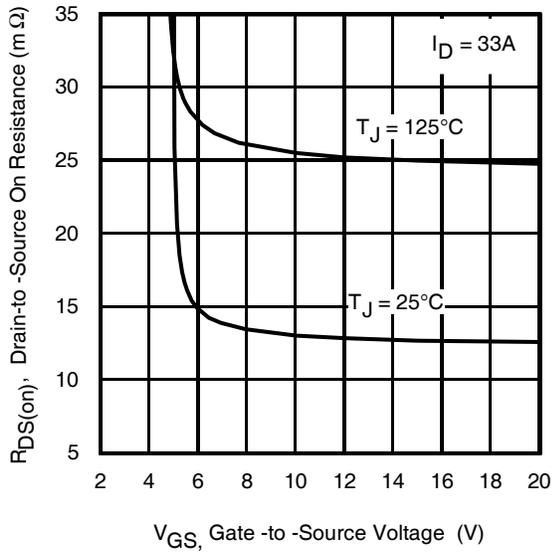


Fig 12. On-Resistance vs. Gate Voltage

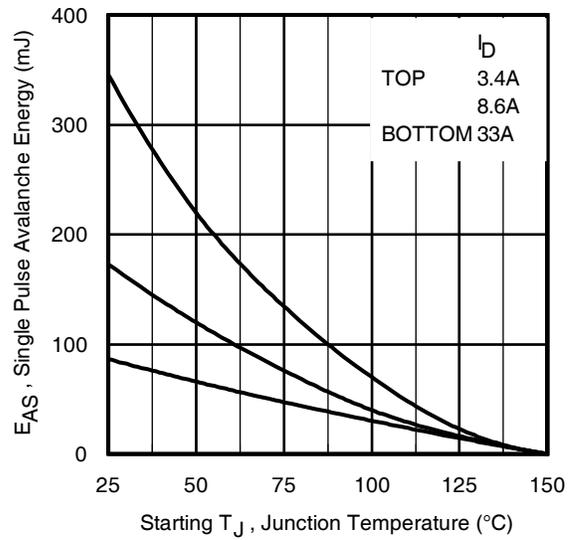


Fig 13. Maximum Avalanche Energy vs. Drain Current

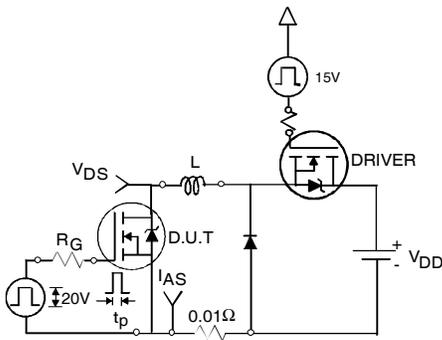


Fig 14a. Unclamped Inductive Test Circuit

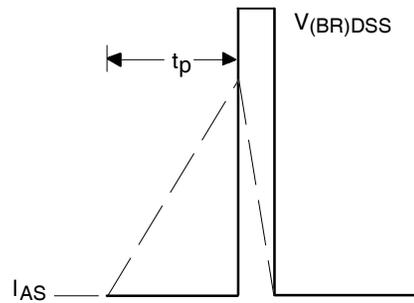


Fig 14b. Unclamped Inductive Waveforms

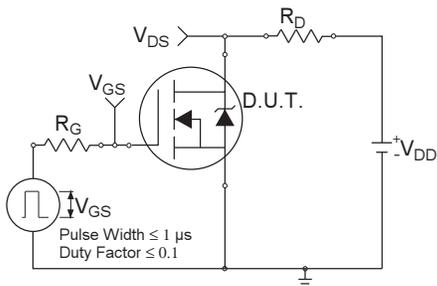


Fig 15a. Switching Time Test Circuit

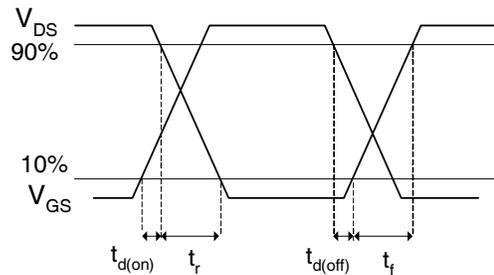


Fig 15b. Switching Time Waveforms

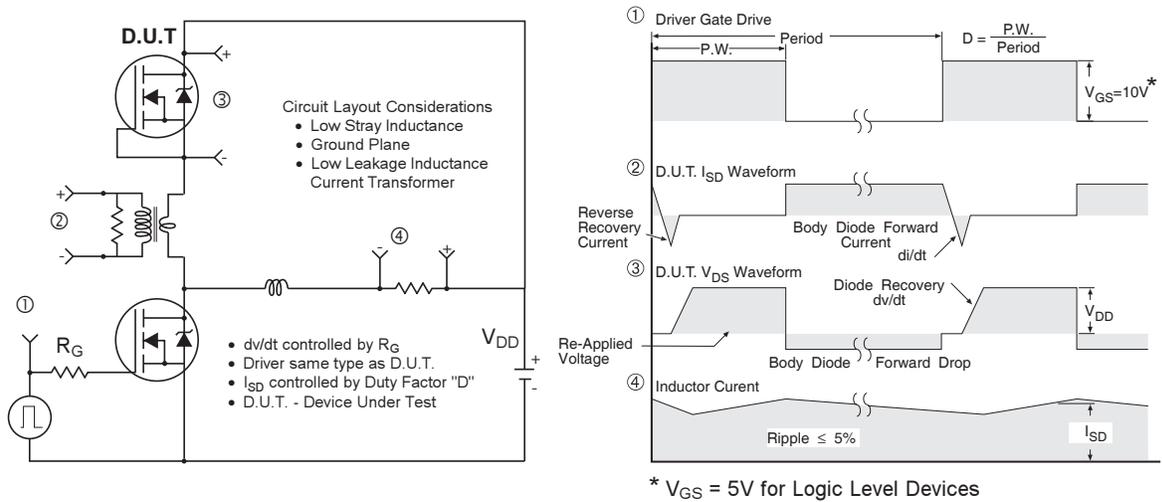


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

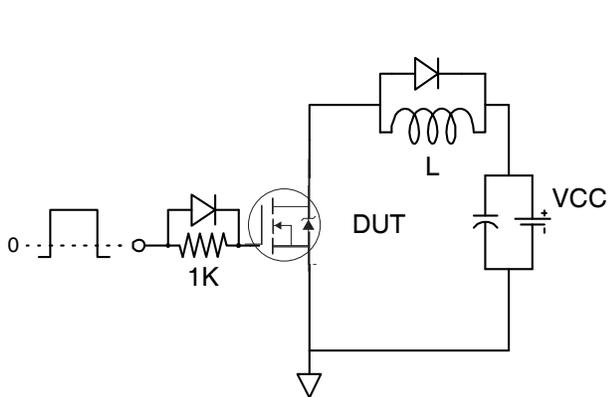


Fig 17. Gate Charge Test Circuit

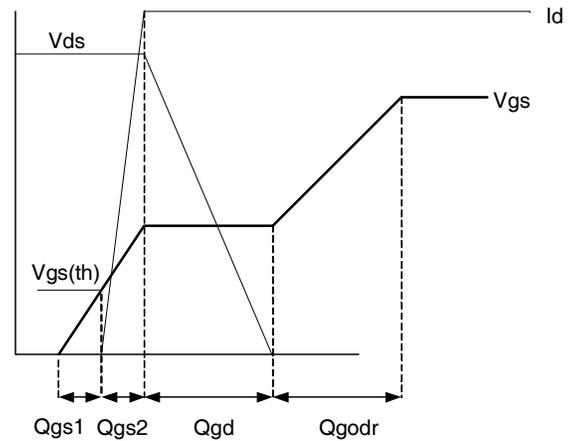
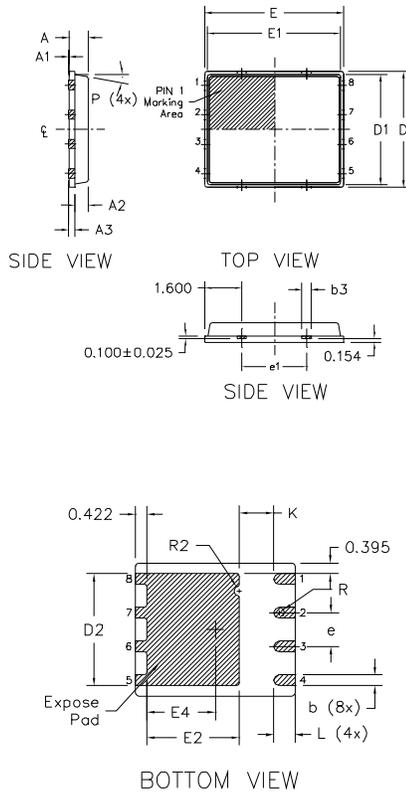


Fig 18. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details



| DIM SYMBOL | MILLIMETERS | | INCH | |
|---------------|-------------|-------|------------|--------|
| | MIN | MAX | MIN | MAX |
| A | 0.800 | 0.900 | 0.0315 | 0.0543 |
| A1 | 0.000 | 0.050 | 0.0000 | 0.0020 |
| A3 | 0.200 REF | | 0.0079 REF | |
| b | 0.350 | 0.470 | 0.0138 | 0.0185 |
| b1 | 0.025 | 0.125 | 0.0010 | 0.0049 |
| b2 | 0.210 | 0.410 | 0.0083 | 0.0161 |
| b3 | 0.150 | 0.450 | 0.0059 | 0.0177 |
| D | 5.000 BSC | | 0.1969 BSC | |
| D1 | 4.750 BSC | | 0.1870 BSC | |
| D2 | 4.100 | 4.300 | 0.1614 | 0.1693 |
| E | 6.000 BSC | | 0.2362 BSC | |
| E1 | 5.750 BSC | | 0.2264 BSC | |
| E2 | 3.380 | 3.780 | 0.1331 | 0.1488 |
| e | 1.270 REF | | 0.0500 REF | |
| e1 | 2.800 REF | | 0.1102 REF | |
| K | 1.200 | 1.420 | 0.0472 | 0.0559 |
| L | 0.710 | 0.900 | 0.0280 | 0.0354 |
| P | 0° | 12° | 0° | 12° |
| R | 0.200 REF | | 0.0079 REF | |
| R2 | 0.150 | 0.200 | 0.0059 | 0.0079 |

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

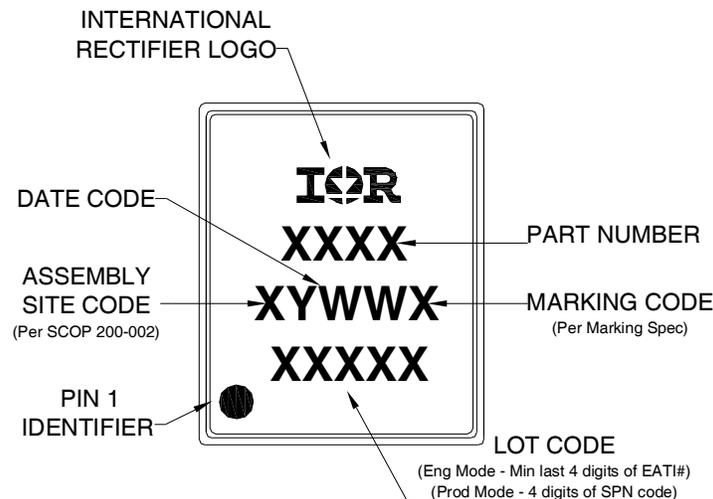
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

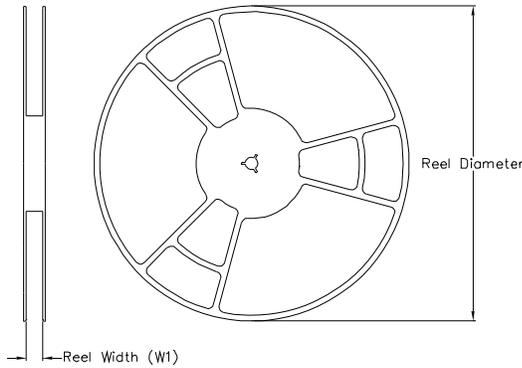
PQFN 5x6 Part Marking



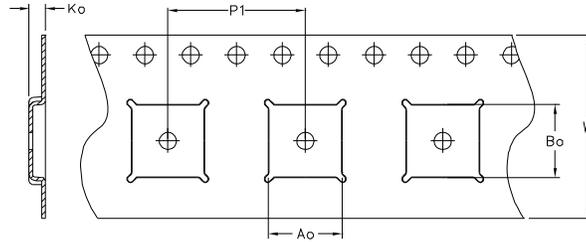
Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

PQFN 5x6 Tape and Reel

REEL DIMENSIONS

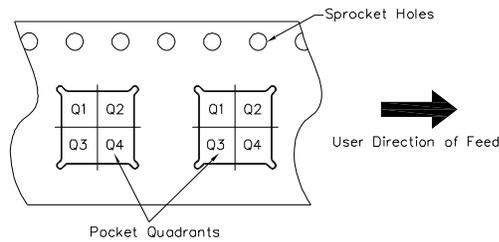


TAPE DIMENSIONS



| CODE | DESCRIPTION |
|------|---|
| Ao | Dimension design to accommodate the component width |
| Bo | Dimension design to accommodate the component length |
| Ko | Dimension design to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

| Package Type | Reel Diameter (Inch) | QTY | Reel Width W1 (mm) | Ao (mm) | Bo (mm) | Ko (mm) | P1 (mm) | W (mm) | Pin 1 Quadrant |
|--------------|----------------------|------|--------------------|---------|---------|---------|---------|--------|----------------|
| 5 X 6 PQFN | 13 | 4000 | 12.4 | 6.300 | 5.300 | 1.20 | 8.00 | 12 | Q1 |

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

| | | |
|----------------------------|---|--|
| Qualification level | Industriid ^{††} (per JEDEC JESD47F ^{†††} guidelines) | |
| Moisture Sensitivity Level | PQFN 5mm x 6mm | MSL1 (per JEDEC J-STD-020D ^{†††}) |
| RoHS compliant | Yes | |

† Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.
 Please contact your International Rectifier sales representative for further information:
<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.16\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 33\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

Revision History

| Date | Comment |
|-----------|--|
| 1/7/2014 | <ul style="list-style-type: none"> • Updated ordering information to reflect the End-of-Life (EOL) of the mini-reel option (EOL notice #259). • Updated data sheet with the new IR corporate template. |
| 3/16/2015 | <ul style="list-style-type: none"> • Updated package outline and tape and reel on pages 7 and 8. |



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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